

Si Avalanche Photodiode (APD) Series

400-1100nm



● Product Description

The Si avalanche photodetector module integrates a low-noise APD detector, a low-noise broadband transimpedance amplifier, ultra-low-noise isolated power supply, high-voltage power supply, and APD temperature compensation. The isolated power supply ensures that the output signal is not affected by external power sources. APD temperature compensation improves the stability of the detection module. The avalanche photodetector features high gain, high sensitivity, high bandwidth, and low noise characteristics.

● Part Number

APD-500M-B-FC/APC

● Product features

Low noise, high gain、 Built-in high-voltage power supply、 APD temperature compensation、 Compact structure、 Built-in low-noise isolated power supply

● Application area

dical field、 Printing、 Fiber laser systems

General Parameters

PN#	APD-100 M-B	APD-200 M-B	APD-300 M-B	APD-400 M-B	APD-500 M-B	APD-1G -B	APD-2G -B	Unit
Detector Type	Si							
Wavelength	400~1100							nm
Bandwidth	100M	200M	300M	400M	500M	1G	2G	Hz
Responsivity	25	25	25	25	25	25	25	A/W@850 nm
Transimpedance Gain	300K	300K	300K	300K	300K	300K	300K	V/W
Output Impedance	50	50	50	50	50	50	50	Ω
Saturation Power	13	13	13	13	13	13	30	uW
NEP	0.18	0.18	0.18	0.18	0.18	0.2	0.2	pW/√ (Hz)
Output Coupling Method	DC/AC	DC/AC	DC/AC	DC/AC	DC	AC	AC	
Power Supply Voltage	5	5	5	5	5	12	12	V
Power Supply Current	0.5(max)	0.5(max)	0.5(max)	0.5(max)	0.5(max)	0.5(max)	0.5(max)	A
Optical Input	FC/APC (Free-space optical optional)							
RF Output	SMA							
Dimensions	65*50*20							mm